AMENDMENTS

In the specification

On page 8, please amend the paragraph beginning on line 15 as follows:

The second-conductivity-type clad layer is suitably a semiconductor layer containing, for example, Al, Ga, As, In and/or P as constituent atoms. More specifically, it is preferable that the clad layer be formed of $(Ga_{1-y}Al_y)_mIn_{1-m}P$ (wherein, for example, y=0.7, m=0.5, though ~~x and z~~ y and m may be such that $0.1 \leqq y \leqq 0.9$, and $0.2 \leqq m \leqq 0.8$). In the case where the active layer is formed of GaAlInP and the second-conductivity-type clad layer is also formed of GaAlInP, it is preferable that the Al mixed crystal ratio of the active layer be lower than that of the second-conductivity-type clad layer. More specifically, the Al mixed crystal ratio of the second-conductivity-type clad layer may be about 0.5 to 0.9 and, more preferably, about 0.7. The concentration of impurities in the second-conductivity-type clad layer is suitably, for example, in the range of about 1×10^{17} to 4×10^{17} cm^{-3}. The thickness of the clad layer is suitably, for example, about 0.7 to 1.0 μm.